said gate line, said light shielding film being connected to a potential so that an increase in parasitic capacitance between the light shielding film and the gate line is suppressed, a load amount on the gate line is suppressed, and a delay of gate potential is small;

said first semiconductive layer being located beneath the capacitance line and spaced from the lights shielding film by a gate insulating film and substantially in register with the light shielding film at a location not beneath the gate line;

a second substrate disposed opposite to said first substrate and with a predetermined interval; and

a liquid crystal layer held between said first substrate and said second substrate.

- (Amended) A liquid crystal display device according to claim 1, wherein said light shielding film is disposed between said substrate and said pixel transistor.
- 3. (Amended) A liquid crystal display device according to claim 1, wherein said light shielding film is disposed over said pixel transistor.
 - 4. A liquid crystal display device, comprising:
- a first substrate and a second substrate opposite said first substrate with a liquid crystal layer held between said first and second substrate;
 - a light shielding film formed on said first substrate;

a pixel transistor formed of a first silicon layer on said first substrate, said light shielding film for shielding against incident or scattered light;

a gate line;

a capacitance line, said capacitance line and said gate line formed of a second silicon layer;

a gate insulating film;

said light shielding film formed substantially beneath said first silicon layer and extending so as to terminate at a location which is not beneath said gate line, and disposed under said capacitance line, said light shielding film being connected to a fixed potential so that an increase in parasitic capacitance between the light shielding film and the gate line is suppressed, a load amount on said gate line is suppressed and a delay of gate potential is small.

- 5. The liquid crystal display device as set forth in claim 4, wherein said first silicon layer is located beneath said capacitance line and spaced from said light shielding film by a [first] gate insulating [layer] film and substantially in register with said light [emitting] shielding film at a location not beneath said gate line.
- 6. The liquid crystal display device as set forth in claim 5 wherein said light shielding film is made from a metal and is connected to a metal layer having a fixed potential.

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Please add the following new claims:

- 7. (newly-added) A liquid crystal display device comprising:
 - a first substrate;
 - a semiconductor layer formed on said first substrate;
 - a gate line;
 - a capacitance line;
- a light shielding film formed substantially beneath said semiconductor layer and extending so as to terminate at a location which is not beneath said gate line and disposed under said capacitance line, the light shielding film being connected to a fixed potential so that an increase in parasitic capacitance between the light shielding film and the gate line is suppressed, a load amount on the gate line is suppressed and a delay of gate potential is small;

the first semiconductor layer being located beneath the capacitance line and spaced from the light shielding film by a gate insulating film and substantially in register with the light shielding film at a location not beneath the gate line;

the light shielding film being made from metal and connected to a metal layer having a fixed potential.

8. (newly-added) The liquid crystal display device according to claim 7, wherein said first semiconductor layer is a silicon layer.

REMARKS

This is a full and timely response to the non-final Official